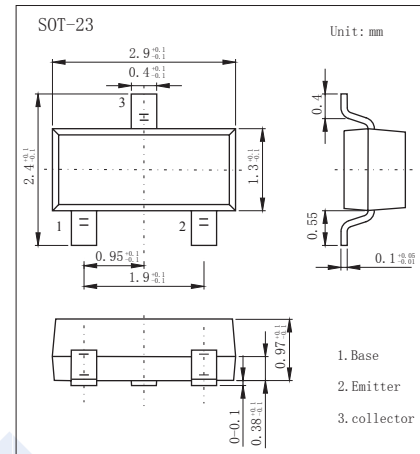


NPN Transistors

2SC3661

■ Features

- Collector Current Capability $I_C=300\text{mA}$
- Collector Emitter Voltage $V_{CE0}=25\text{V}$



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	30	V
Collector - Emitter Voltage	V_{CEO}	25	
Emitter - Base Voltage	V_{EBO}	15	
Collector Current - Continuous	I_C	300	mA
Collector Current - Pulse	I_{CP}	500	
Collector Power Dissipation	P_C	200	mW
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 125	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	30			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	25			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	15			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 10\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 200 \text{ mA}, I_B = 4 \text{ mA}$			0.5	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 200 \text{ mA}, I_B = 4 \text{ mA}$			1.2	
DC current gain	h_{FE}	$V_{CE} = 5\text{V}, I_C = 10 \text{ mA}$	800		3200	
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{V}, f = 1 \text{ MHz}$		2.7		pF
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 10 \text{ mA}$		250		MHz

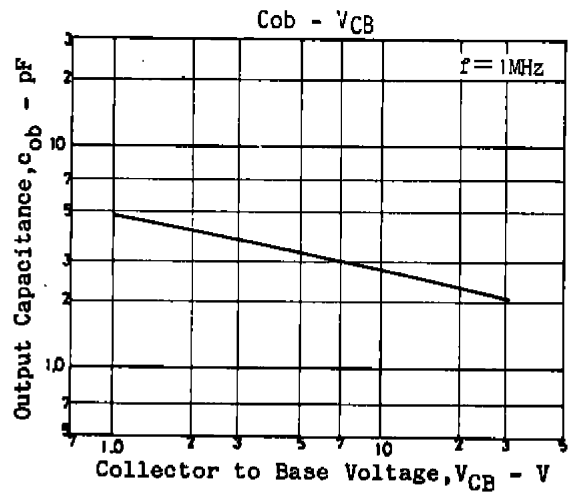
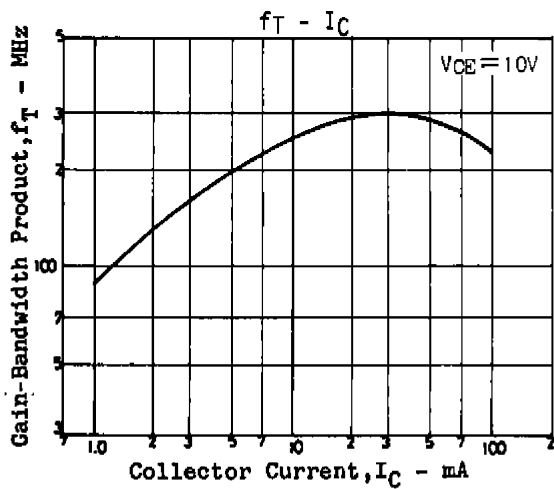
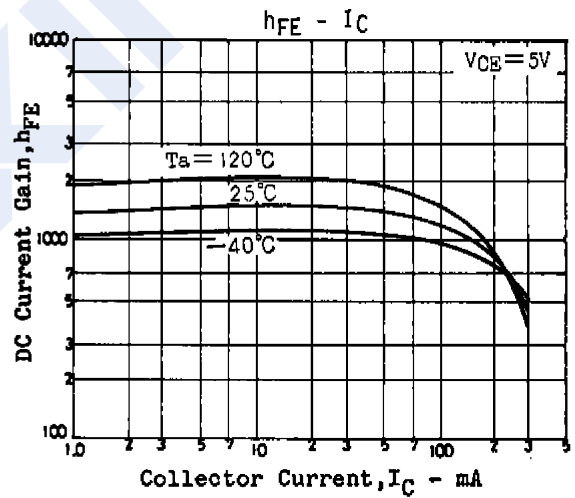
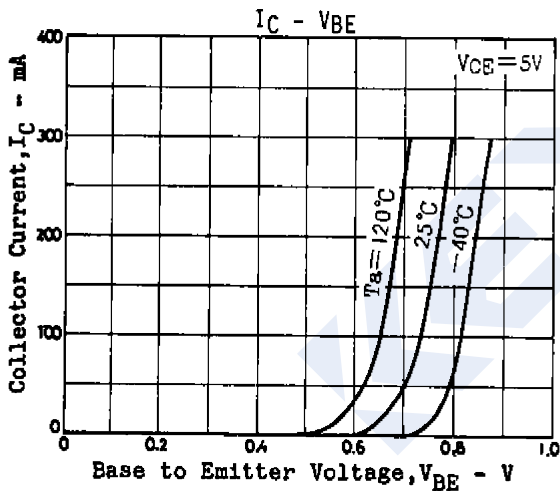
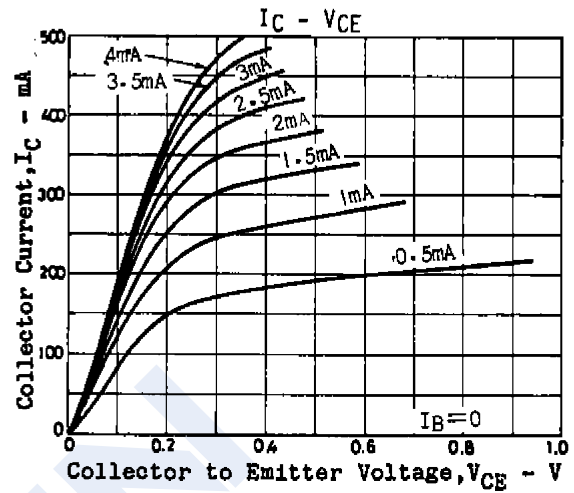
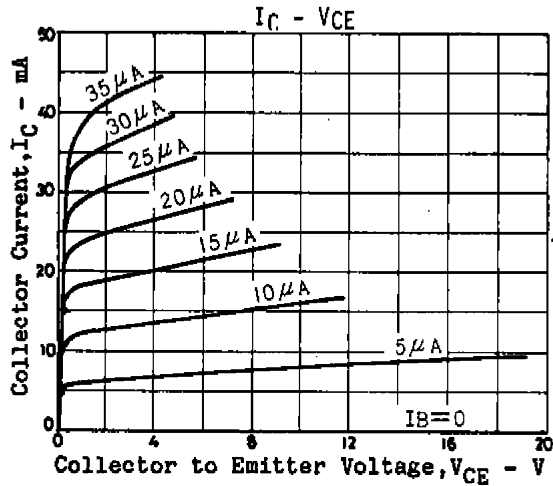
■ Marking

Marking	FY
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■ Typical Characteristics



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■ Typical Characteristics

